



Atty. Docket No. 8013-1074

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Box AF

Hidemitsu AOKI et al.

Confirmation No. 6696

Serial No. 09/715,000

GROUP 2825

Filed November 20, 2000

Examiner Chuong A. Luu

IMPROVED SEMICONDUCTOR WAFER
SURFACE AND METHOD OF TREATING
A SEMICONDUCTOR WAFER SURFACE

RESPONSE AFTER FINAL REJECTION

Commissioner for Patents

Washington, D.C. 20231

Sir:

This responds to the Official Action of August 14, 2002. Claims 1-33 and 57-62 are present in the application.

Claims 1, 4, 6 and 57-58 are rejected as being anticipated by NISHITANI et al. 5,670,421. This rejection is respectfully traversed.

Claim 1 of the present application recites forming a copper-diffusion stopper insulating film over a surface of a semiconductor substrate. By way of example, Figure 2C of the present application shows Si_3N_4 film 18 serving as a copper-diffusion stopper insulating film formed over copper interconnection 17 of the substrate 10.

The Official Action states that column 2, lines 22-63 of NISHITANI et al. disclose forming a copper-diffusion stopper insulating film over a surface of a semiconductor substrate. In

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Response (AF)
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